NSN 5961-00-409-8331

Thyristor Semiconductor Device - Page 1 of 1

View Online at https://aerobasegroup.com/nsn/5961-00-409-8331

Inclosure Material:

Metal

Overall Length:

1.500 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

Between 1.031 inches and 1.062 inches

Thread Size:

0.500 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

600.0 breakover voltage, dc

Current Rating Per Characteristic:

70.00 amperes forward current, average

Power Rating Per Characteristic:

0.5 watts small-signal input power, common-collector peak

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: pnpn

Test Data Document:

01425--5-855 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Thread Series Designator:

Unf

Terminal Type And Quantity:

3 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0